

ABSTRACT

The present invention addresses the problem of providing a mask blank with which mask patterns and hard mask patterns can be made finer and pattern quality can be improved. To solve the problem, a mask blank (100), which has a structure in which a pattern formation thin-film (3) and a hard mask film (4) are laminated in this order on a substrate (1), is configured so that; the hard mask film (4) is formed from a material containing silicon, oxygen, and nitrogen; the nitrogen content is between 2% and 18%, inclusive; and an Si2p narrow spectrum obtained by X-ray photoelectron spectroscopy has the maximum peak at a binding energy of 103 eV or greater.